

### STI400N4F6, STP400N4F6

# N-channel 40 V, 120 A STripFET™ VI DeepGATE™ Power MOSFET in I<sup>2</sup>PAK and TO-220 packages

Datasheet - preliminary data

#### **Features**

Order codes	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STI400N4F6 STP400N4F6	40 V	< 1.7 mΩ	120 A <sup>(1)</sup>

- 1. Limited by package
- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

#### **Applications**

■ Switching applications

#### **Description**

These devices are N-channel Power MOSFETs developed using the 6th generation of STripFET<sup>TM</sup> DeepGATE<sup>TM</sup> technology, with a new gate structure. The resulting Power MOSFETs exhibits the lowest  $R_{DS(on)}$  in all packages.

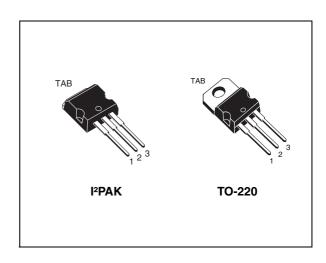


Figure 1. Internal schematic diagram

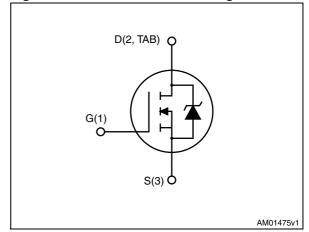


Table 1. Device summary

Order codes	Marking	Package	Packaging
STI400N4F6	400N4F6	I <sup>2</sup> PAK	Tube
STP400N4F6	400114170	TO-220	iube

### **Contents**

1	Electrical ratings	3
2	Electrical characteristics	4
3	Package mechanical data	6
4	Revision history	10

## 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage	40	V
V <sub>GS</sub>	Gate-source voltage	± 20	٧
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> = 25 °C	120	Α
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> = 100 °C	120	Α
I <sub>DM</sub> <sup>(1)</sup>	Drain current (pulsed)	480	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	300	W
	Derating factor	2	W/°C
T <sub>stg</sub>	Storage temperature - 55 to 175		°C
T <sub>j</sub>	Operating junction temperature	- 55 10 175	

<sup>1.</sup> Current limited by package

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	0.5	°C/W
R <sub>thj-a</sub>	Thermal resistance junction-ambient max	62.5	°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purpose	300	°C

### 2 Electrical characteristics

(T<sub>CASE</sub> = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage (V <sub>GS</sub> = 0)	I <sub>D</sub> = 250 μA	40			V
	Zero gate voltage	V <sub>DS</sub> = 40 V			1	μΑ
I <sub>DSS</sub>	Drain current (V <sub>GS</sub> = 0)	$V_{DS} = 40 \text{ V}, T_{C} = 125 ^{\circ}\text{C}$			100	μΑ
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3		4.5	٧
R <sub>DS(on)</sub>	Static drain-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 60 A		TBD	1.7	mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C <sub>iss</sub>	Input capacitance			20000		pF
C <sub>oss</sub>	Output capacitance	$V_{DS} = 25 \text{ V, f} = 1 \text{ MHz,}$	_	1740	-	pF
$C_{rss}$	Reverse transfer capacitance	V <sub>GS</sub> = 0		1305		pF
$Q_g$	Total gate charge	V 00 V 1 100 A		377		nC
$Q_{gs}$	Gate-source charge	$V_{DD} = 20 \text{ V}, I_D = 120 \text{ A},$ $V_{GS} = 10 \text{ V}$	-	TBD	-	nC
$Q_{gd}$	Gate-drain charge	VGS - 10 V		TBD		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub>	Turn-on delay time Rise time	$V_{DD} = 20 \text{ V}, I_{D} = 60 \text{ A}$ $R_{G} = 4.7 \Omega V_{GS} = 10 \text{ V}$	-	TBD	-	ns
t <sub>d(off)</sub>	Turn-off-delay time Fall time		-	TBD	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max	Unit
I <sub>SD</sub> <sup>(1)</sup>	Source-drain current		-		120	Α
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)		-		480	Α
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	$I_{SD} = 120 \text{ A}, V_{GS} = 0$	1		1.1	V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 120 \text{ A}, V_{DD} = 32 \text{ V}$ di/dt = 100 A/ $\mu$ s, $T_j = 150 ^{\circ}\text{C}$	-	TBD		ns nC A

<sup>1.</sup> Current limited by package

<sup>2.</sup> Pulsed: pulse duration = 300  $\mu$ s, duty cycle 1.5%

### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. I<sup>2</sup>PAK (TO-262) mechanical data

DIM.		mm.	
DIIVI.	min.	typ	max.
Α	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
С	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
е	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

 $\begin{array}{c} L2 \\ \\ D \\$ 

Figure 2. I<sup>2</sup>PAK (TO-262) drawing

Table 9. TO-220 type A mechanical data

D:		mm	
Dim.	Min.	Тур.	Max.
Α	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
Е	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 3. TO-220 type A drawing

## 4 Revision history

Table 10. Document revision history

Date	Revision	Changes
13-Aug-2012	1	First release.

#### **Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



#### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by STMicroelectronics manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B